

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.

جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



AO4600

Complementary Enhancement Mode Field Effect Transistor

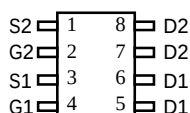


General Description

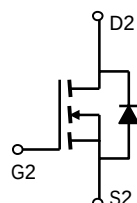
The AO4600 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs form a high-speed power inverter, suitable for a multitude of applications. Standard Product AO4600 is Pb-free (meets ROHS & Sony 259 specifications). AO4600L is a Green Product ordering option. AO4600 and AO4600L are electrically identical.

Features

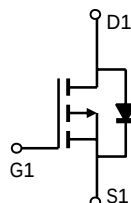
n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 6.9A (V_{GS} = 10V)$	-5A ($V_{GS} = -10V$)
$R_{DS(ON)}$	
< 27m Ω	< 49m Ω ($V_{GS} = -10V$)
< 32m Ω	< 64m Ω ($V_{GS} = -4.5V$)
< 50m Ω	< 120m Ω ($V_{GS} = -2.5V$)



SOIC-8



n-channel



p-channel

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 12	± 12	V
Continuous Drain Current ^A	$T_A=25^\circ C$	6.9	-5	A
	$T_A=70^\circ C$	5.8	-4.2	
Pulsed Drain Current ^B	I_{DM}	40	-30	
Power Dissipation	$T_A=25^\circ C$	2	2	W
	$T_A=70^\circ C$	1.44	1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ C$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	48	62.5	$^\circ C/W$
Maximum Junction-to-Ambient ^A		74	110	$^\circ C/W$
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	35	40	$^\circ C/W$

n-channel MOSFET Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.7	1	1.4	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	25			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6.9A T _J =125°C		22.6 33	27 40	mΩ
		V _{GS} =4.5V, I _D =6.0A		27	32	mΩ
		V _{GS} =2.5V, I _D =5A		42	50	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A	12	16		S
V _{SD}	Diode Forward Voltage	I _S =1A		0.71	1	V
I _S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		858	1050	pF
C _{oss}	Output Capacitance			110		pF
C _{rss}	Reverse Transfer Capacitance			80		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.24	4	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =6.9A		9.6	12	nC
Q _{gs}	Gate Source Charge			1.65		nC
Q _{gd}	Gate Drain Charge			3		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =2.2Ω, R _{GEN} =6Ω		5.7		ns
t _r	Turn-On Rise Time			13		ns
t _{D(off)}	Turn-Off DelayTime			37		ns
t _f	Turn-Off Fall Time			4.2		ns
t _{rr}	Body Diode Reverse Recovery time	I _F =5A, dI/dt=100A/μs		15.5	20	ns
Q _{rr}	Body Diode Reverse Recovery charge	I _F =5A, dI/dt=100A/μs		7.9		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL N-CHANNEL ELECTRICAL AND THERMAL CHARACTERISTICS

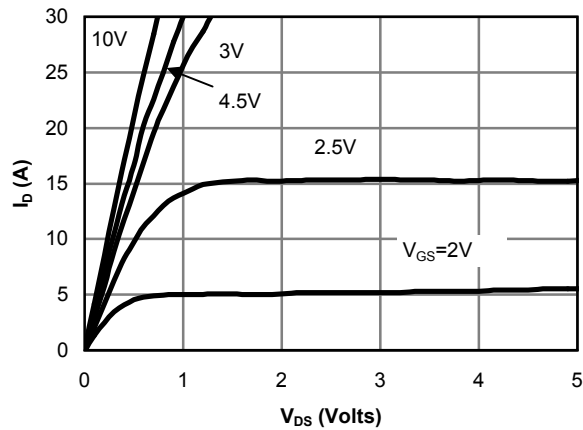


Fig 1: On-Region Characteristics

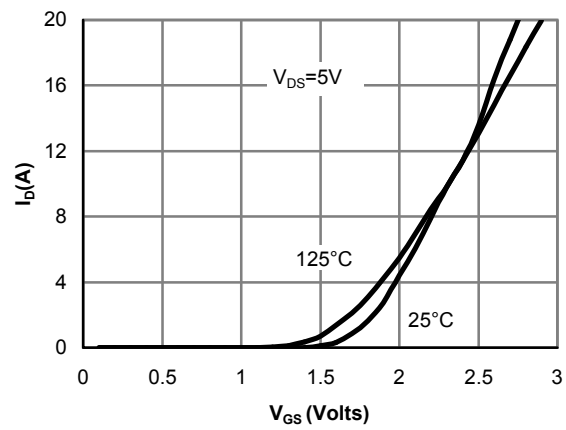


Figure 2: Transfer Characteristics

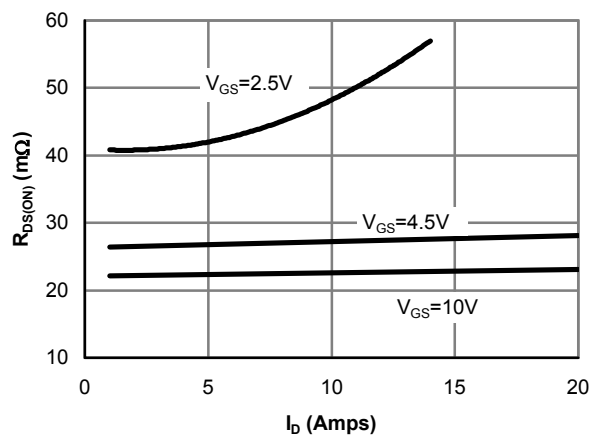


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

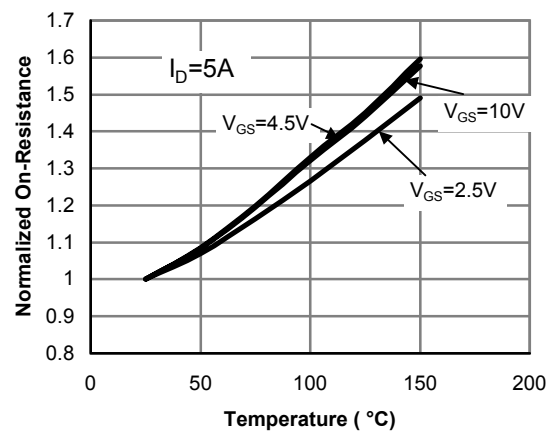


Figure 4: On-Resistance vs. Junction Temperature

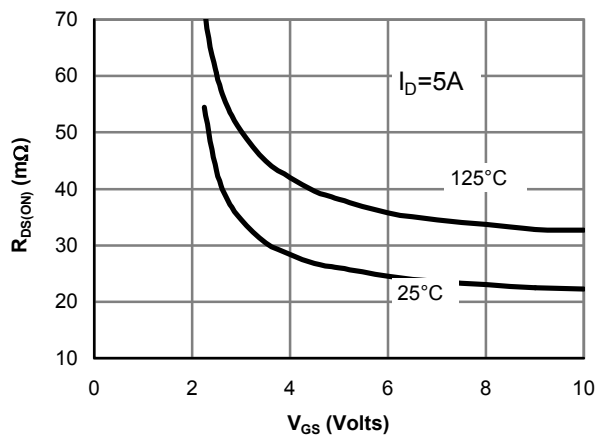


Figure 5: On-Resistance vs. Gate-Source Voltage

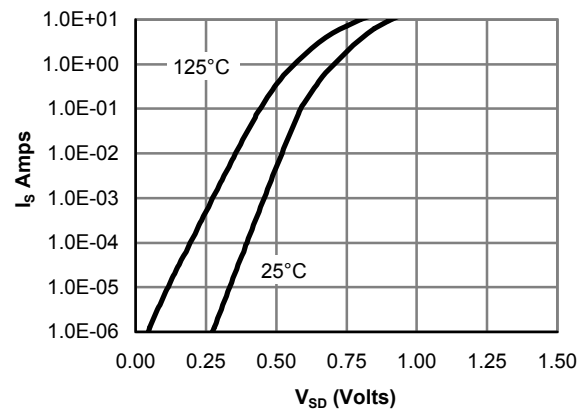


Figure 6: Body diode characteristics

TYPICAL N-CHANNEL ELECTRICAL AND THERMAL CHARACTERISTICS

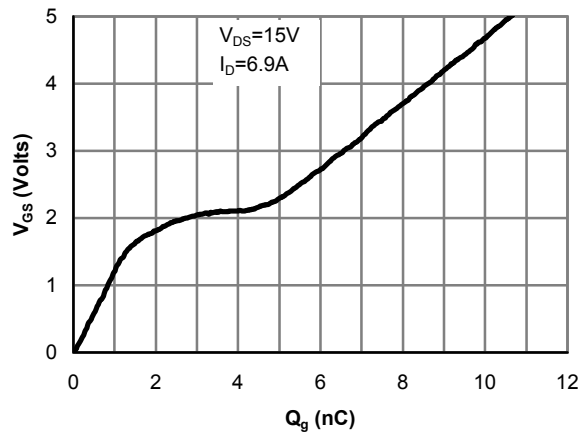


Figure 7: Gate-Charge characteristics

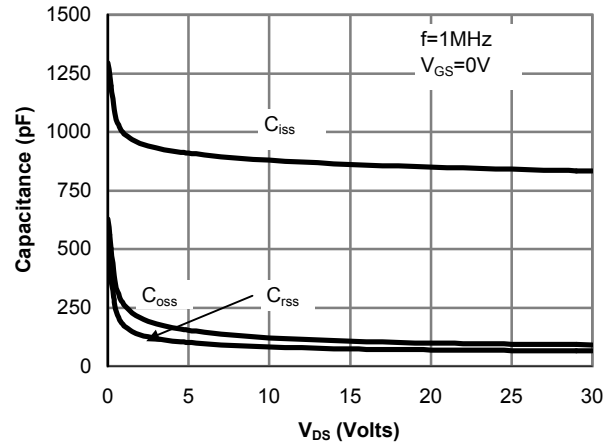


Figure 8: Capacitance Characteristics

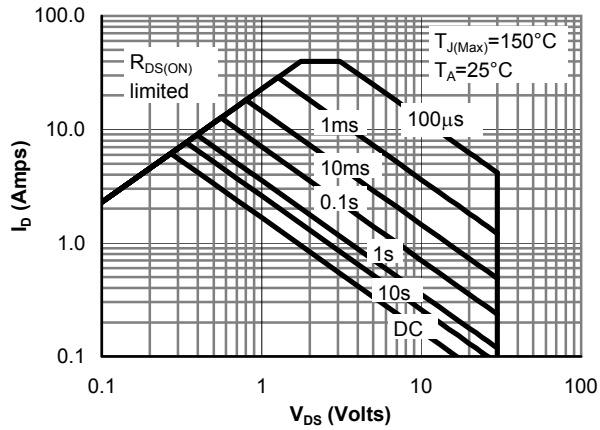


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

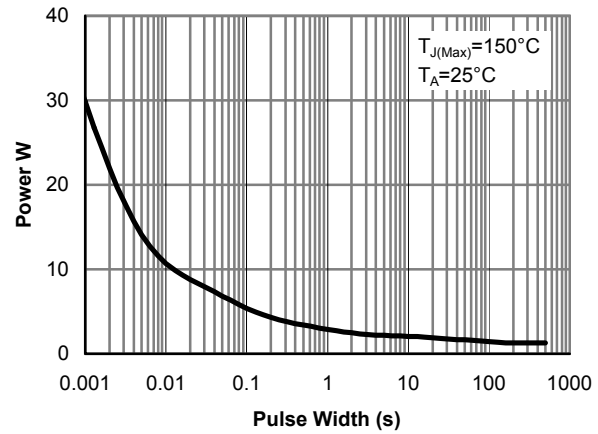


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

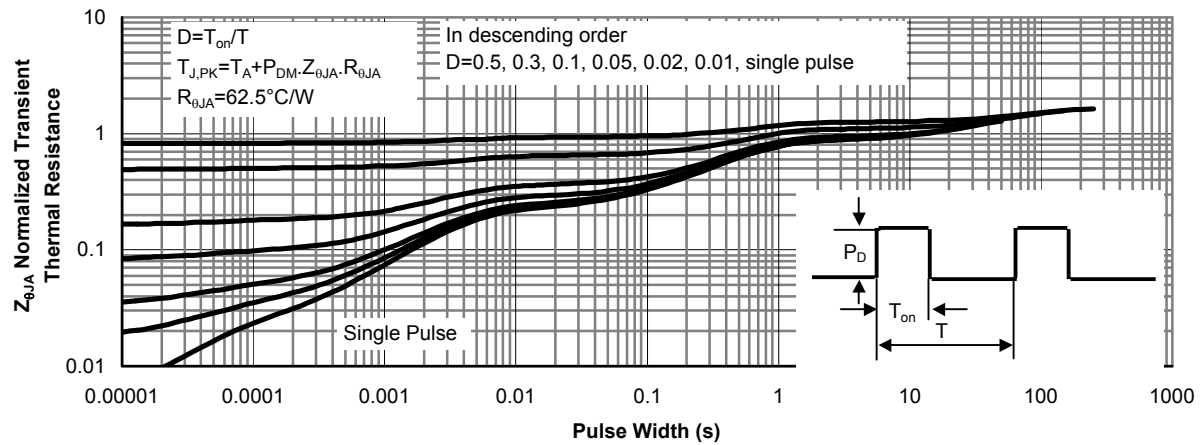


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-0.7	-1	-1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$, $V_{DS}=-5\text{V}$	-25			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-5\text{A}$ $T_J=125^\circ\text{C}$		42.5	49 74	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-4\text{A}$		54	64	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-1\text{A}$		80	120	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-5\text{A}$	7	11		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current				-3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		952	1200	pF
C_{oss}	Output Capacitance			103		pF
C_{rss}	Reverse Transfer Capacitance			77		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		5.9	30	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-5\text{A}$		9.5	12	nC
Q_{gs}	Gate Source Charge			2		nC
Q_{gd}	Gate Drain Charge			3.1		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=3\Omega$, $R_{GEN}=6\Omega$		12		ns
t_r	Turn-On Rise Time			4		ns
$t_{D(off)}$	Turn-Off DelayTime			37		ns
t_f	Turn-Off Fall Time			12		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		21	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		13		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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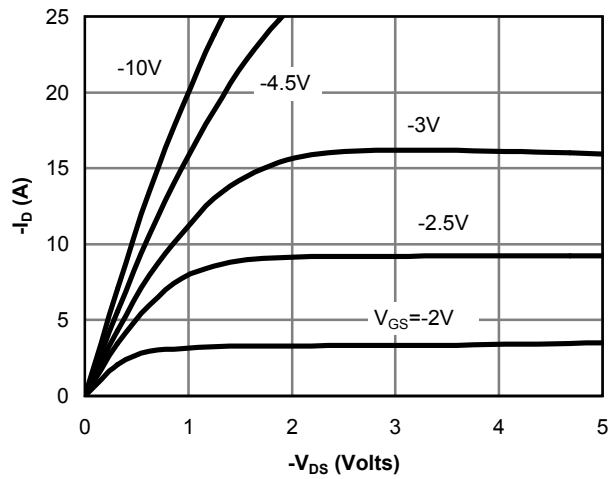


Fig 1: On-Region Characteristics

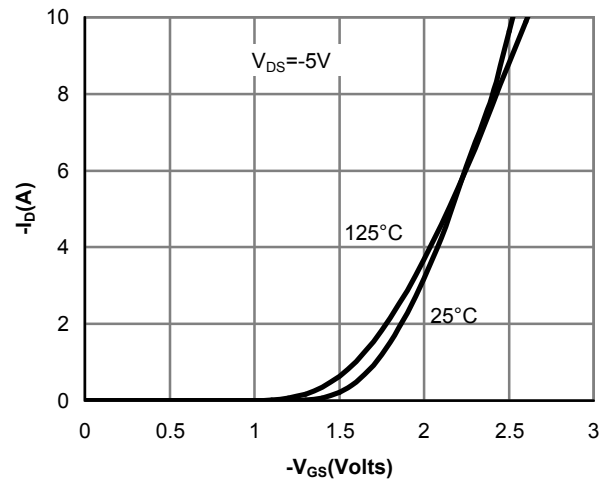


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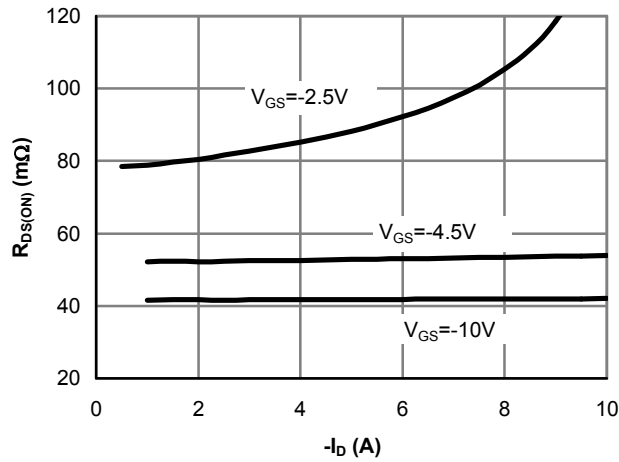


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

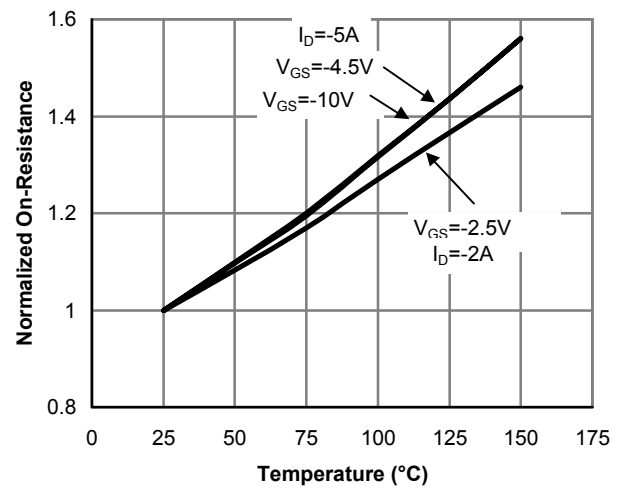


Figure 4: On-Resistance vs. Junction Temperature

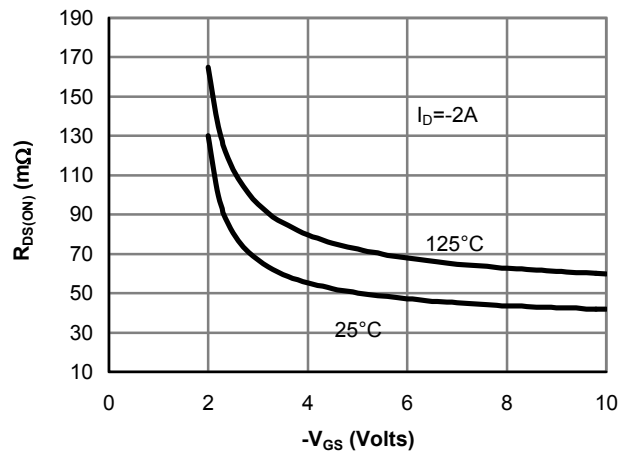


Figure 5: On-Resistance vs. Gate-Source Voltage

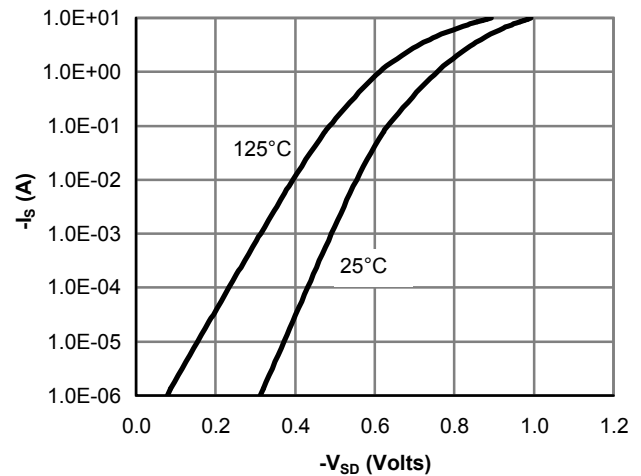


Figure 6: Body-Diode Characteristics

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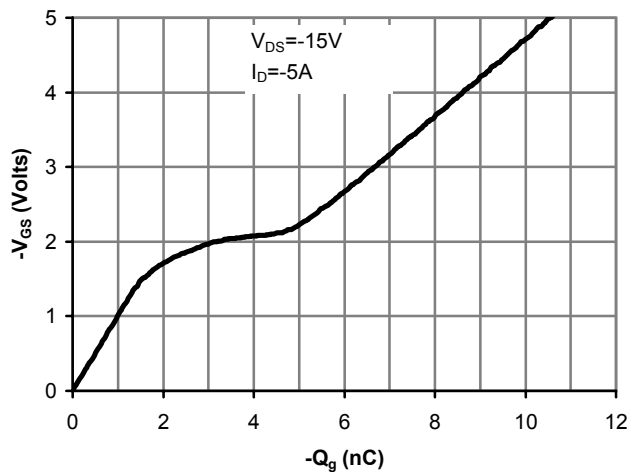


Figure 7: Gate-Charge Characteristics

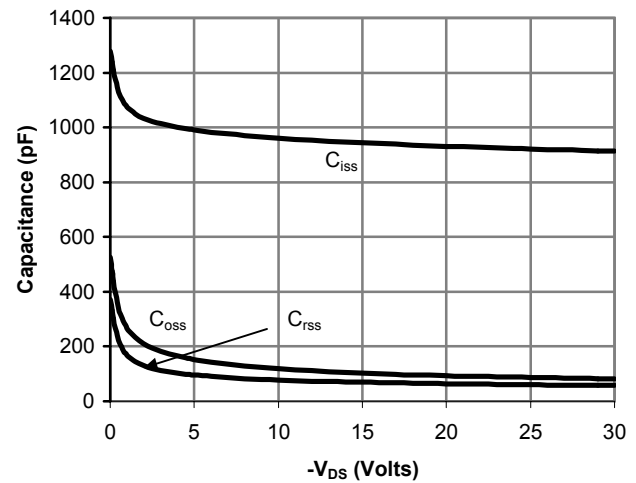


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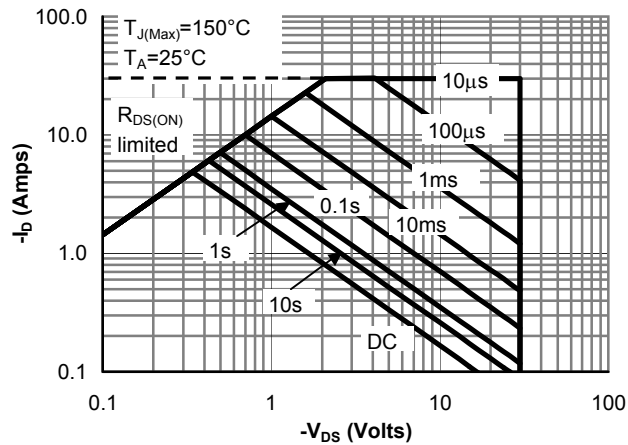


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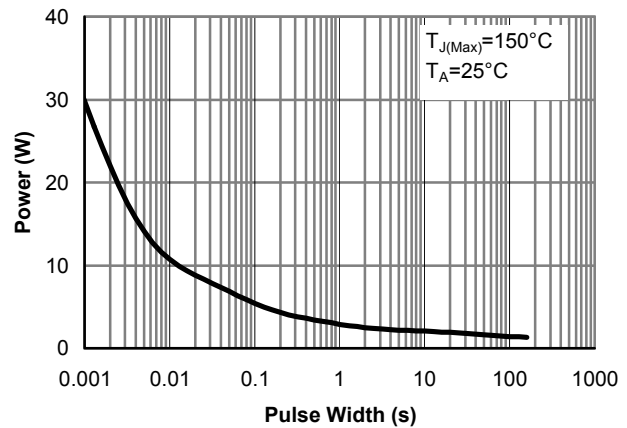


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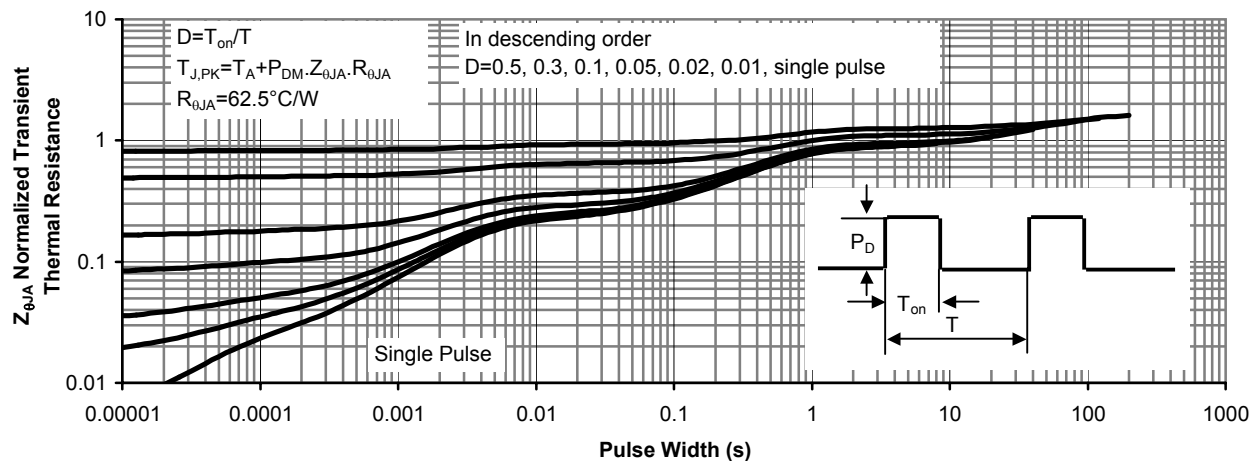


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